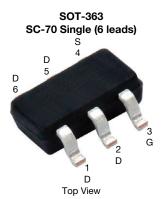
## SQ1421EDH

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**Vishay Siliconix** 

### Automotive P-Channel 60 V (D-S) MOSFET



#### Marking Code: 9D

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	-60			
$R_{DS(on)} (\Omega)$ at $V_{GS} = -10 V$	0.290			
$R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 V$	0.395			
I <sub>D</sub> (A)	-1.6			
Configuration	Single			
Package	SC-70			

#### **FEATURES**

- TrenchFET<sup>®</sup> power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>g</sub> and UIS tested
- Typical ESD protection: 800 V

P-Channel MOSFET

• Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

(3) G O



HALOGEN

FREE

(1, 2, 5, 6) D

(4) S

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-source voltage	V <sub>DS</sub>	-60	V			
Gate-source voltage	V <sub>GS</sub>	V <sub>GS</sub> ± 20				
Continuous drain current	T <sub>C</sub> = 25 °C ª	1	-1.6			
	T <sub>C</sub> = 125 °C	l <sub>D</sub>	-1			
Continuous source current (diode conduction) <sup>a</sup>	I <sub>S</sub>	-1.6	А			
Pulsed drain current <sup>b</sup>	I <sub>DM</sub>	-6.7				
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	-8			
Single pulse avalanche energy		E <sub>AS</sub>	3.2	mJ		
Maximum power dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	Р	2.7	W		
Maximum power dissipation	T <sub>C</sub> = 125 °C	P <sub>D</sub>	0.5	٧V		
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-ambient	tion-to-ambient PCB mount <sup>c</sup>		125	°C/W		
nction-to-foot (drain)		R <sub>thJF</sub>	45	C/ W		

#### Notes

- a. Package limited
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %
- c. When mounted on 1" square PCB (FR4 material)

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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		-60	-	-	v
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{GS}$ , $I_D$ = -250 $\mu$ A	-1.5	-2.0	-2.5	v
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 V, V_{GS} = \pm 12 V$		-	± 5	μA
Gale-source leakage		V <sub>DS</sub> =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 5	mA
		$V_{GS} = 0 V$	V <sub>DS</sub> = -60 V	-	-	-1	μA
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS}$ = -60 V, $T_{J}$ = 125 °C	-	-	-50	
		$V_{GS} = 0 V$	$V_{DS} = -60 \text{ V}, \text{ T}_{J} = 150 ^{\circ}\text{C}$	-	-	-150	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = -10 V$	$V_{DS} \le -5 V$	-5	-	-	Α
		V <sub>GS</sub> = -10 V	I <sub>D</sub> = -2 A	-	0.230	0.290	Ω
Drain aquiras on state registence a	P	$V_{GS} = -10 \text{ V}$	I <sub>D</sub> = -2 A, T <sub>J</sub> = 125 °C	-	-	0.470	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = -10 V$	I <sub>D</sub> = -2 A, T <sub>J</sub> = 150 °C	-	-	0.566	
		V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -1 A	-	0.305	0.395	
Forward transconductance b	9fs	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1.5 A		-	3	-	S
Dynamic <sup>b</sup>							
Input capacitance	C <sub>iss</sub>			-	284	355	pF
Output capacitance	Coss	$V_{GS} = 0 V$	$V_{DS} = -25 V, f = 1 MHz$	-	36	45	
Reverse transfer capacitance	C <sub>rss</sub>			-	28	35	
Total gate charge <sup>c</sup>	Qg			-	3.6	5.4	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS}$ = -4.5 V	$V_{DS} = -30 \text{ V}, \text{ I}_{D} = -1 \text{ A}$	-	1.2	-	nC
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	1.7	-	
Gate resistance	R <sub>g</sub>		f = 1 MHz		6.05	9	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	44	66	
Rise time <sup>c</sup>	t <sub>r</sub>	$\label{eq:VDD} \begin{array}{l} V_{DD} = -30 \mbox{ V}, \mbox{ R}_L = 30 \ \Omega \\ I_D \cong -1 \mbox{ A}, \mbox{ V}_{GEN} = -4.5 \mbox{ V}, \mbox{ R}_g = 1 \ \Omega \end{array}$		-	25	38	ns
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	13	20	
Fall time <sup>c</sup>	t <sub>f</sub>			-	9	14	
Source-Drain Diode Ratings and Cha	racteristics <sup>b</sup>						
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	-6.7	Α
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> = -0.5 A, V <sub>GS</sub> = 0 V		-	-0.8	-1.2	V

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

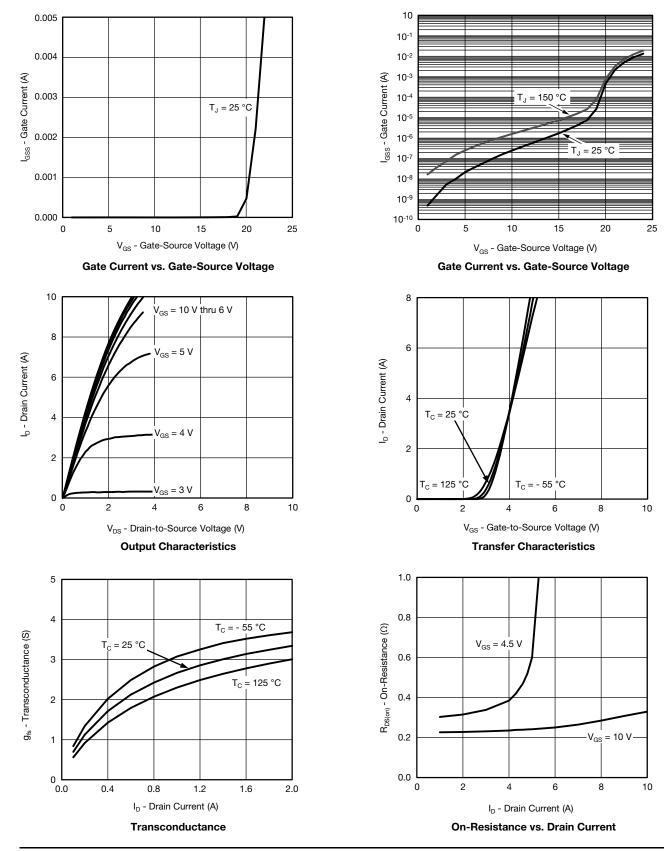
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### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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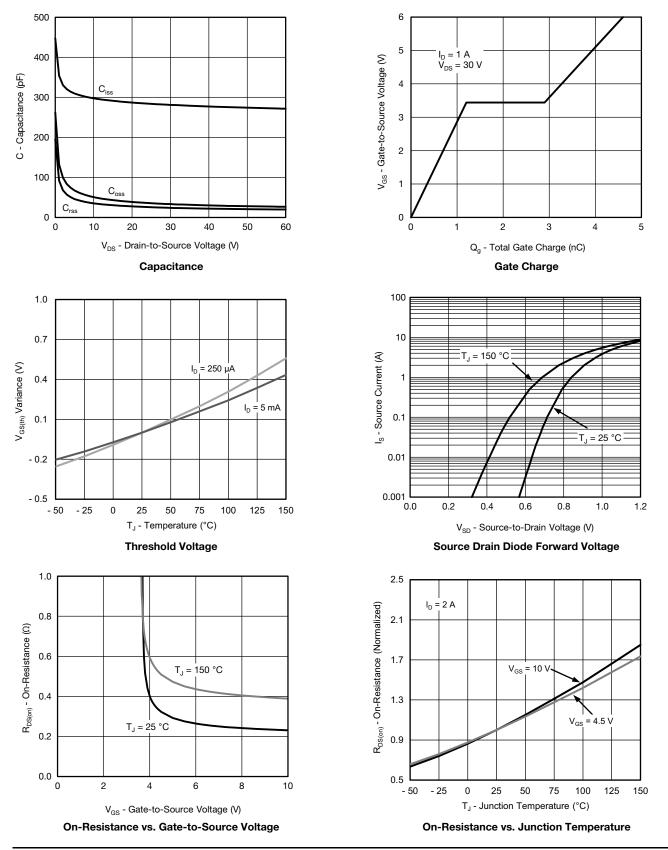
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#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



S17-1782-Rev. B, 27-Nov-17

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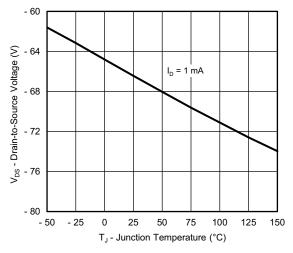
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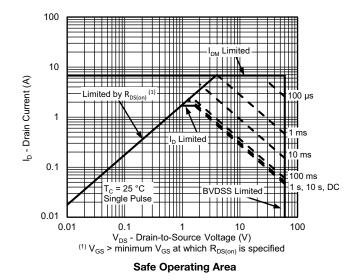


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### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



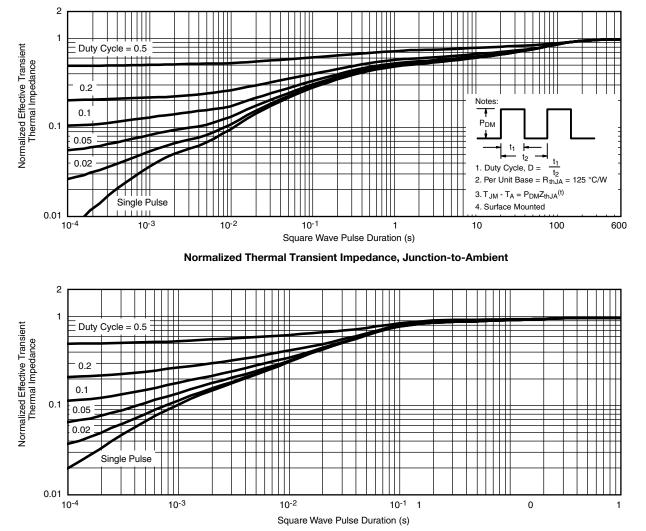
Drain Source Breakdown vs. Junction Temperature





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#### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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# Package Information Vishay Siliconix

### SC-70: 6-LEADS





	MILLIMETERS			INCHES		
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.90	-	1.10	0.035	-	0.043
A <sub>1</sub>	-	-	0.10	-	-	0.004
A <sub>2</sub>	0.80	-	1.00	0.031	-	0.039
b	0.15	-	0.30	0.006	-	0.012
С	0.10	-	0.25	0.004	-	0.010
D	1.80	2.00	2.20	0.071	0.079	0.087
Е	1.80	2.10	2.40	0.071	0.083	0.094
E <sub>1</sub>	1.15	1.25	1.35	0.045	0.049	0.053
е	0.65BSC			0.026BSC		
e <sub>1</sub>	1.20	1.30	1.40	0.047	0.051	0.055
L	0.10	0.20	0.30	0.004	0.008	0.012
٩	7°Nom				7°Nom	
ECN: S-03946—Rev. B, 09-Jul-01 DWG: 5550						

# **Application Note 826**

Vishay Siliconix



**RECOMMENDED MINIMUM PADS FOR SC-70: 6-Lead** 



Recommended Minimum Pads Dimensions in Inches/(mm)

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